

IN THE CLAIMS

Please amend claims 1-5 as follows:

- C1
1. (Thrice Amended) An integrated circuit comprising:
a dielectric layer formed over a substrate;
a damascene structure in the dielectric layer, the damascene structure comprising a bottom surface and first and second sidewalls;
a conductor located in the damascene structure, the conductor comprising a conductive material; and
a liner layer lining the bottom surface and sidewalls of the damascene structure and encapsulating the conductor by contacting a top surface of the conductor, the liner layer imparts a random grain orientation in the conductive material of the conductor to improve electromigration lifetime of the conductor.
 2. (Twice Amended) An integrated circuit of claim 1, wherein a conductive material of the liner comprises a random grain orientation.
 3. (Twice Amended) An integrated circuit of claim 1, wherein a conductive material of the liner comprises an amorphous character.
 4. (Twice Amended) An integrated circuit of claim 1, wherein a conductive material of the liner is chosen from a group consisting essentially of titanium nitride, tantalum and tantalum nitride.